

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	153	MISFET and (doped adj layer)	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/16 12:20
L2	3	1 and (dummy adj gate adj electrode)	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/16 12:22
L3	6	1 and dummy	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/16 12:23
L4	269	MISFET and dummy	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/16 12:23
L5	66	MISFET and (dummy adj gate)	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/16 12:26
L6	1	5 and (dummy adj MISFET)	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/16 12:24
L7	65	5 and substrate	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/16 12:26
L8	35	7 and doped	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/16 12:26
L9	4	(dummy adj MISFET) and layer	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/04/16 12:27